



# STP165N10F4

N-channel 100 V, 4.4 mΩ, 120 A TO-220  
STripFET™ DeepGATE™ Power MOSFET

## Features

Order code	V <sub>DSS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
STP165N10F4	100 V	< 5.5 mΩ	120 A

- N-channel enhancement mode
- 100% avalanche rated
- Low gate charge
- Very low on-resistance

## Application

Switching applications

## Description

The STP165N10F4 is an N-channel enhancement mode Power MOSFET built with STripFET™ DeepGATE™ technology with a new gate structure. The product is tailored to minimize on-resistance.

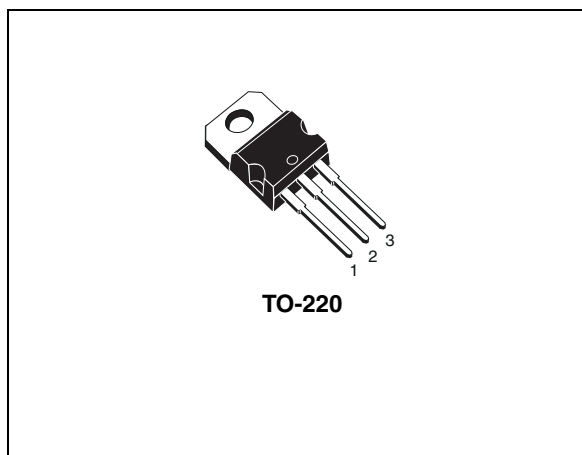


Figure 1. Internal schematic diagram

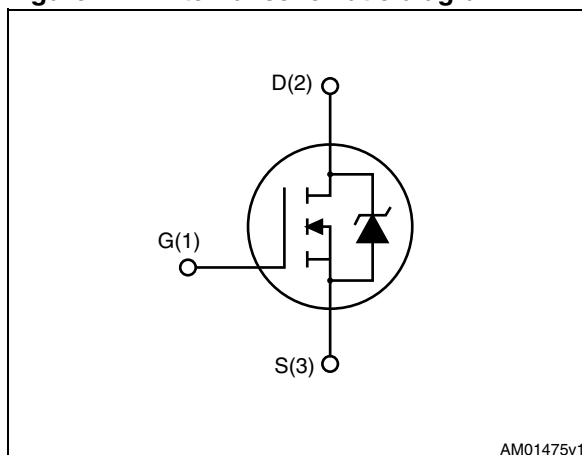


Table 1. Device summary

Order code	Marking	Package	Packaging
STP165N10F4	165N10F4	TO-220	Tube

# Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	100	V
$V_{GS}$	Gate- source voltage	$\pm 20$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	120	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	110	A
$I_{DM}^{(1)}$	Drain current (pulsed)	480	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	315	W
	Derating factor	2.1	W/ $^\circ\text{C}$
$E_{AS}^{(2)}$	Single pulse avalanche energy	500	mJ
$T_{stg}$	Storage temperature	- 55 to 150	$^\circ\text{C}$
$T_j$	Max. operating junction temperature	150	

1. Pulse width limited by safe operating area
2. Starting  $T_j = 25\text{ }^\circ\text{C}$ ,  $I_D = 58\text{ A}$ ,  $V_{DD} = 50\text{ V}$

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.48	$^\circ\text{C}/\text{W}$
$R_{thj-a}$	Thermal resistance junction-ambient max	62.5	$^\circ\text{C}/\text{W}$
$T_l$	Maximum lead temperature for soldering purpose	315	$^\circ\text{C}$

## 2 Electrical characteristics

( $T_{CASE}=25^{\circ}\text{C}$  unless otherwise specified)

**Table 4. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown voltage	$I_D = 250 \mu\text{A}$ , $V_{GS} = 0$	100			V
$I_{DSS}$	Zero gate voltage Drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{max rating}$ $V_{DS} = \text{max rating}$ , $T_C = 125^{\circ}\text{C}$			1 100	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20 \text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250 \mu\text{A}$	2		4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10 \text{ V}$ , $I_D = 60 \text{ A}$		4.4	5.5	$\text{m}\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance			10750		pF
$C_{oss}$	Output capacitance	$V_{DS} = 25 \text{ V}$ , $f = 1 \text{ MHz}$ , $V_{GS} = 0$	-	939	-	pF
$C_{rss}$	Reverse transfer capacitance			603		pF
$Q_g$	Total gate charge	$V_{DD} = 50 \text{ V}$ , $I_D = 120 \text{ A}$ , $V_{GS} = 10 \text{ V}$ <i>(see Figure 14)</i>		192		nC
$Q_{gs}$	Gate-source charge		-	48	-	nC
$Q_{gd}$	Gate-drain charge			62		nC

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on delay time Rise time	$V_{DD} = 50\text{ V}$ , $I_D = 60\text{ A}$ $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$ (see Figure 13)	-	29.6 62	-	ns ns
$t_{d(off)}$ $t_f$	Turn-off-delay time Fall time	$V_{DD} = 50\text{ V}$ , $I_D = 60\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$ (see Figure 13)	-	154 106	-	ns ns

**Table 7. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		120	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		480	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 120\text{ A}$ , $V_{GS} = 0$	-		1.4	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 120\text{ A}$ , $V_{DD} = 80\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$ , $T_j = 150\text{ }^\circ\text{C}$ (see Figure 15)	-	86.8 313 7.2		ns nC A

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

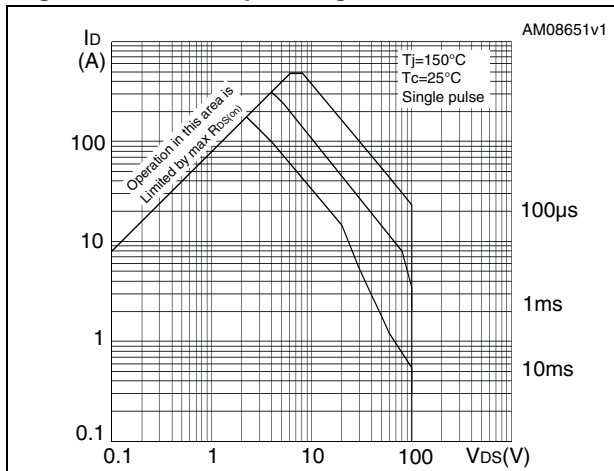


Figure 3. Thermal impedance

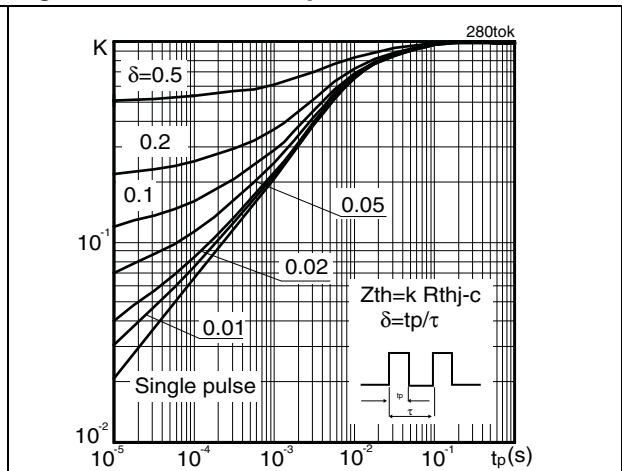


Figure 4. Output characteristics

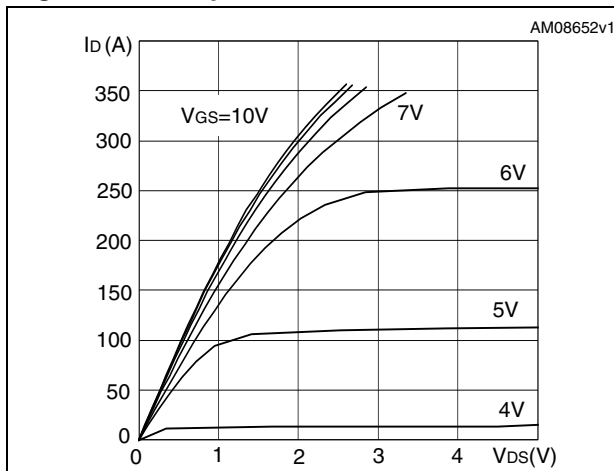


Figure 5. Transfer characteristics

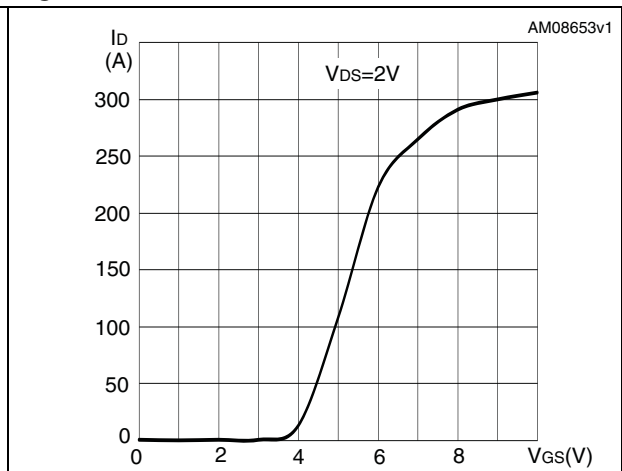


Figure 6. Normalized  $B_{V_{DSS}}$  vs temperature

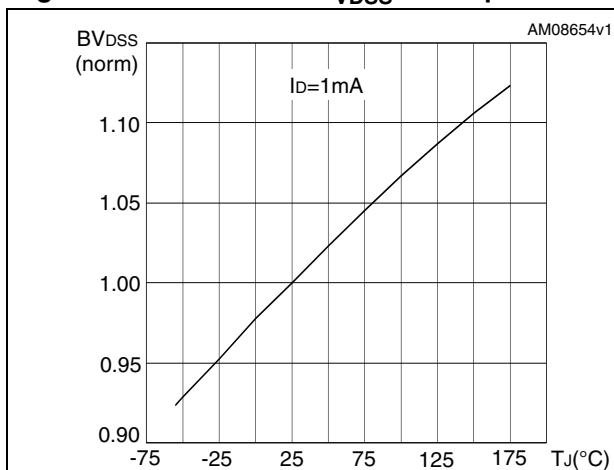


Figure 7. Static drain-source on resistance

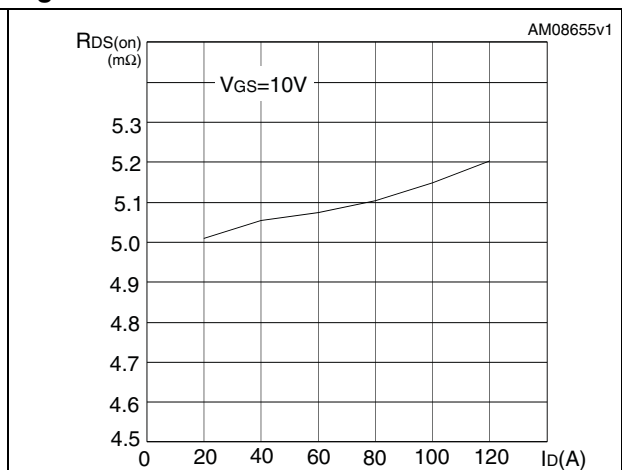


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

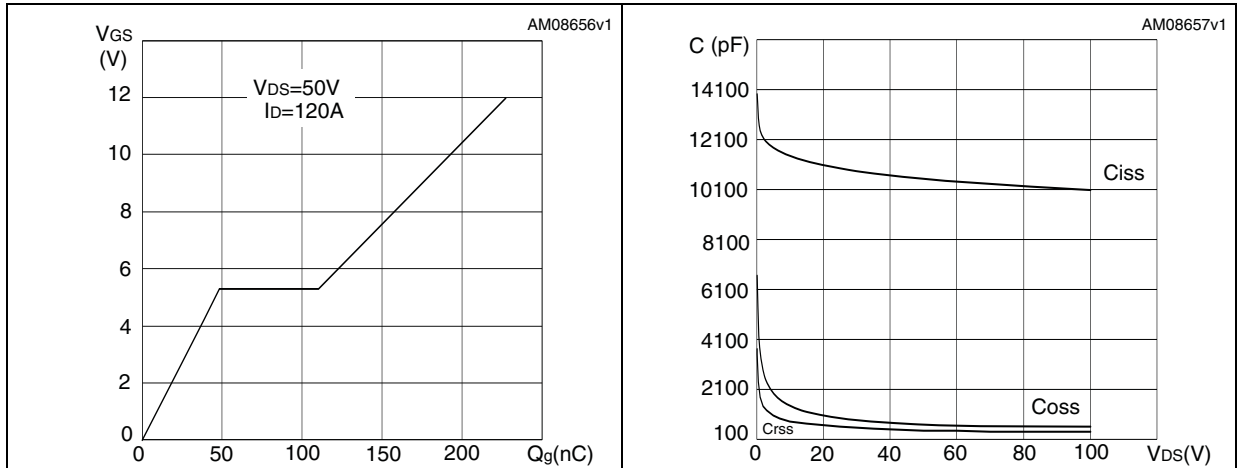


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature

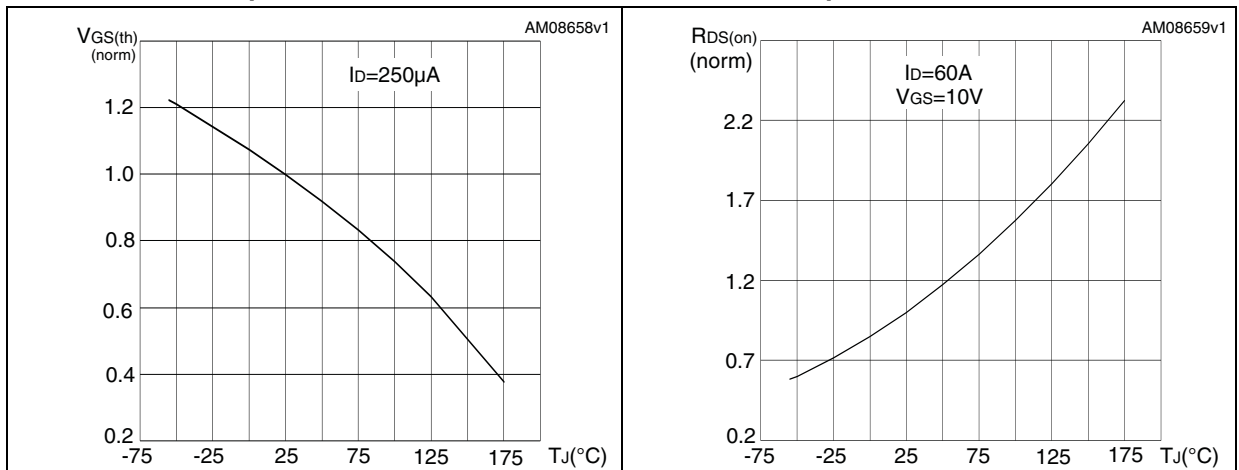
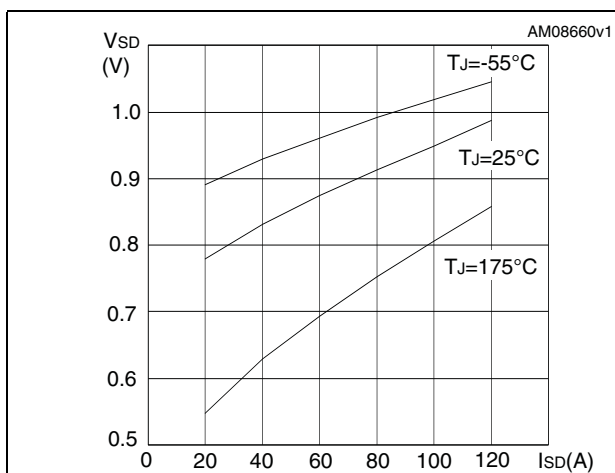


Figure 12. Source-drain diode forward characteristics



### 3 Test circuits

**Figure 13. Switching times test circuit for resistive load**



**Figure 14. Gate charge test circuit**



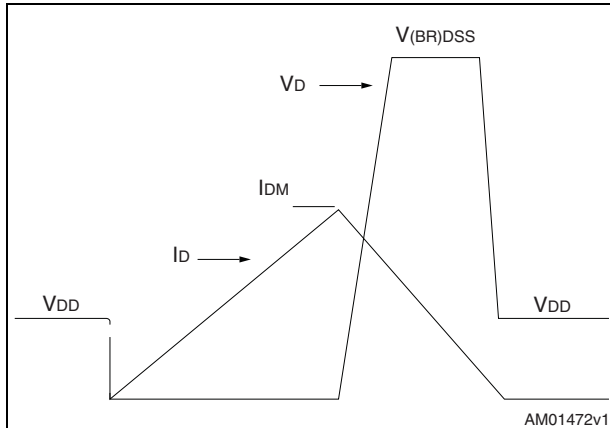
**Figure 15. Test circuit for inductive load switching and diode recovery times**



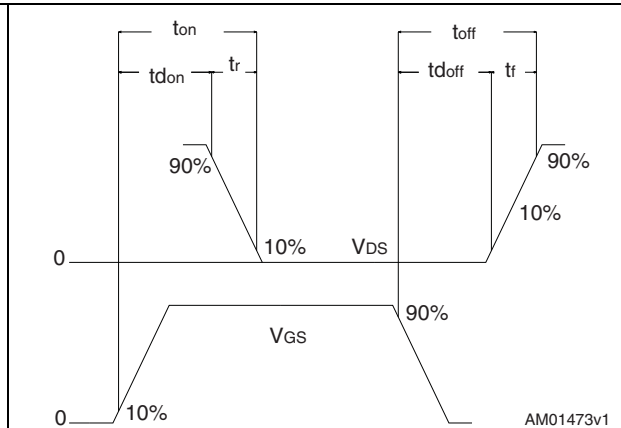
**Figure 16. Unclamped inductive load test circuit**



**Figure 17. Unclamped inductive waveform**



**Figure 18. Switching time waveform**



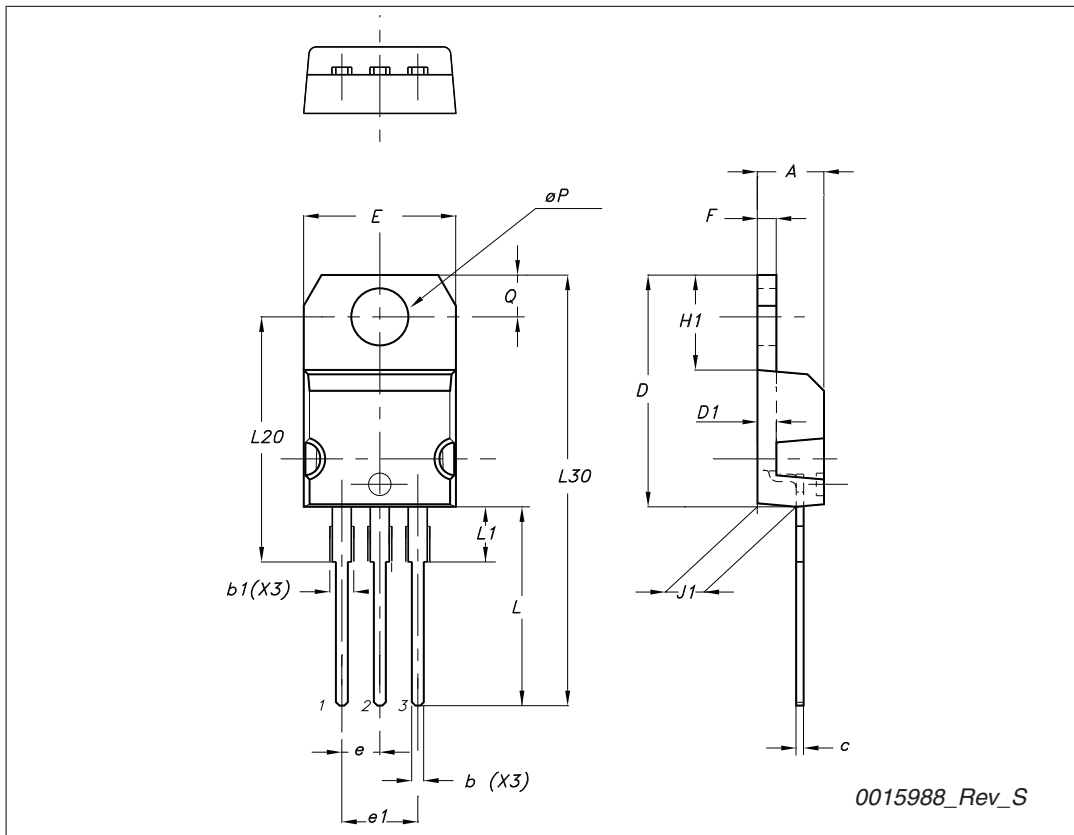


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

**TO-220 type A mechanical data**

Dim	mm		
	Min	Typ	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
∅P	3.75		3.85
Q	2.65		2.95



## 5 Revision history

**Table 8. Document revision history**

Date	Revision	Changes
19-May-2009	1	First release
12-Nov-2010	2	– Removed package H <sup>2</sup> PAK. – Document status promoted from preliminary data to datasheet.

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